

RYC002N05

0.9V Drive Nch MOSFET

● Structure

Silicon N-channel MOSFET

● Features

- 1) High speed switing.
- 2) Small package(SST3).
- 3) Ultra low voltage drive(0.9V drive).

● Application

Switching

● Packaging specifications

Type	Package	Taping
	Code	T316
	Basic ordering unit (pieces)	3000
RYC002N05		○

● Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		V_{DS}	50	V
Gate-source voltage		V_{GS}	±8	V
Drain current	Continuous	I_D	±200	mA
	Pulsed	I_{DP} *1	±800	mA
Source current (Body Diode)	Continuous	I_S	150	mA
	Pulsed	I_{SP} *1	800	mA
Power dissipation		P_D *2	200	mW
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	-55 to +150	°C

*1 $P_w \leq 10\mu s$, Duty cycle $\leq 1\%$

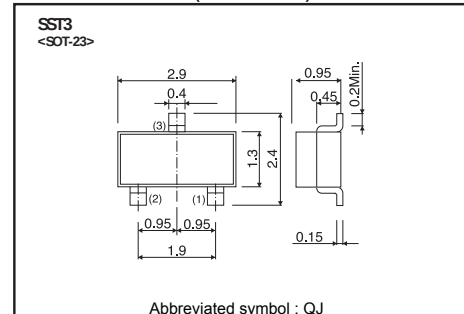
*2 Each terminal mounted on a recommended land.

● Thermal resistance

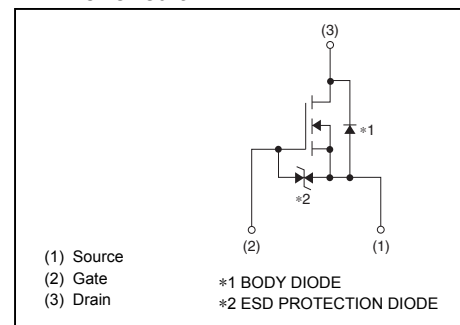
Parameter	Symbol	Limits	Unit
Channel to Ambient	Rth (ch-a)*	625	°C / W

* Each terminal mounted on a recommended land.

● Dimensions (Unit : mm)



● Inner circuit



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● Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	-	-	± 10	μA	$V_{GS} = \pm 8V, V_{DS} = 0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	50	-	-	V	$I_D = 1mA, V_{GS} = 0V$
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	$V_{DS} = 50V, V_{GS} = 0V$
Gate threshold voltage	$V_{GS(th)}$	0.3	-	0.8	V	$V_{DS} = 10V, I_D = 1mA$
Static drain-source on-state resistance	$R_{DS(on)}^*$	-	1.6	2.2	Ω	$I_D = 200mA, V_{GS} = 4.5V$
		-	1.7	2.4		$I_D = 200mA, V_{GS} = 2.5V$
		-	2.0	2.8		$I_D = 200mA, V_{GS} = 1.5V$
		-	2.2	3.3		$I_D = 100mA, V_{GS} = 1.2V$
		-	3.0	9.0		$I_D = 10mA, V_{GS} = 0.9V$
Forward transfer admittance	$ Y_{fs} ^*$	0.2	-	-	S	$I_D = 200mA, V_{DS} = 10V$
Input capacitance	C_{iss}	-	26	-	pF	$V_{DS} = 10V$
Output capacitance	C_{oss}	-	6	-	pF	$V_{GS} = 0V$
Reverse transfer capacitance	C_{rss}	-	3	-	pF	$f = 1MHz$
Turn-on delay time	$t_{d(on)}^*$	-	5	-	ns	$I_D = 100mA, V_{DD} = 25V$
Rise time	t_r^*	-	8	-	ns	$V_{GS} = 4.5V$
Turn-off delay time	$t_{d(off)}^*$	-	17	-	ns	$R_L = 250\Omega$
Fall time	t_f^*	-	43	-	ns	$R_G = 10\Omega$

*Pulsed

● Body diode characteristics (Source-Drain) (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward Voltage	V_{SD}^*	-	-	1.2	V	$I_S = 200mA, V_{GS} = 0V$

*Pulsed